

(19)



JAPANESE PATENT OFFICE

PATENT ABSTRACTS OF JAPAN

(11) Publication number: 59067666 A

(43) Date of publication of application: 17 . 04 . 84

(51) Int. Cl.

H01L 27/10
G11C 17/00

(21) Application number: 57178031

(22) Date of filing: 09 . 10 . 82

(71) Applicant: MITSUBISHI ELECTRIC CORP

(72) Inventor: HANAMURA KOICHI

(54) READ ONLY MEMORY

(57) Abstract:

PURPOSE: To enhance the integration degree more than in a contact ROM and a field ROM by a method wherein a memory element for bits in an ROM is composed of a contact hole and a P-N junction formed thereunder.

CONSTITUTION: The diode ROM using the P-N junction produced by forming a conductive region (N type or P type) 7 having a reverse polarity to that of the following region, with the contact hole 3d as a mask, on a conductive region (P type or N type) 4d formed on a substrate is composed. When any one of bit selection lines 4d becomes at a low level, data readout lines 1d are kept usually at a high level; but, when the contact hole 3d (i.e. diode) is provided in the row corresponding to a selected bit, the readout line therefor is connected to the line of a low level through the diode.

COPYRIGHT: (C)1984,JPO&Japio

